

# XBS013S1CR-G

Schottky Barrier Diode, 100mA, 30V Type

## FEATURES

Ultra Small Package

## APPLICATIONS

Low Current Rectification

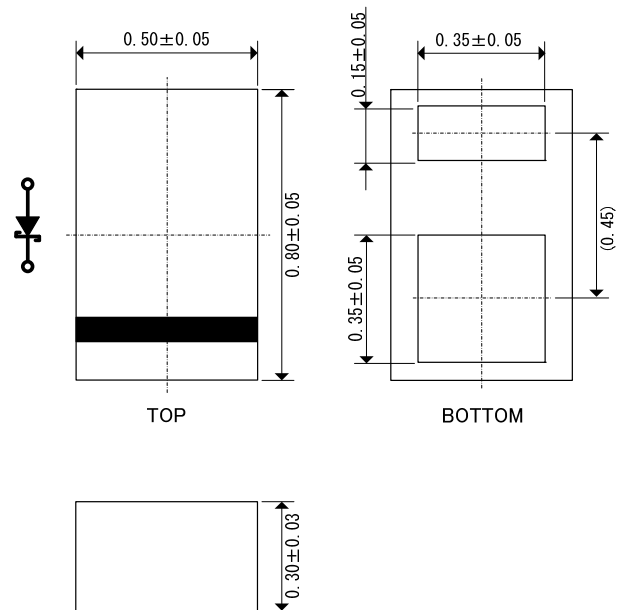
## ABSOLUTE MAXIMUM RATINGS

Ta=25

PARAMETER	SYMBOL	RATINGS	UNITS
Repetitive Peak Voltage	V <sub>RM</sub>	30	V
Reverse Voltage (DC)	V <sub>R</sub>	30	V
Forward Current (Average)	I <sub>F(AV)</sub>	100	mA
Peak Forward Surge Current *1	I <sub>FSM</sub>	0.6	A
Junction Temperature	T <sub>j</sub>	125	
Storage Temperature Range	T <sub>stg</sub>	-55 ~ +125	

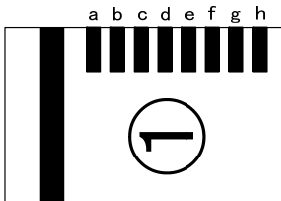
\*1) 60Hz Half sine wave, 1 cycle, Non-Repetitive.

## PACKAGING INFORMATION



Unit: mm

## MARKING RULE



: 3(Product Number)  
a,b,c,d,e,d,e,f,g,h : Lot Number

## PRODUCT NAME

PRODUCT NAME	PACKAGE
XBS013S1CR-G	USP-2B02

\* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

\* The device orientation is fixed in its embossed tape pocket.

## ELECTRICAL CHARACTERISTICS

Ta=25

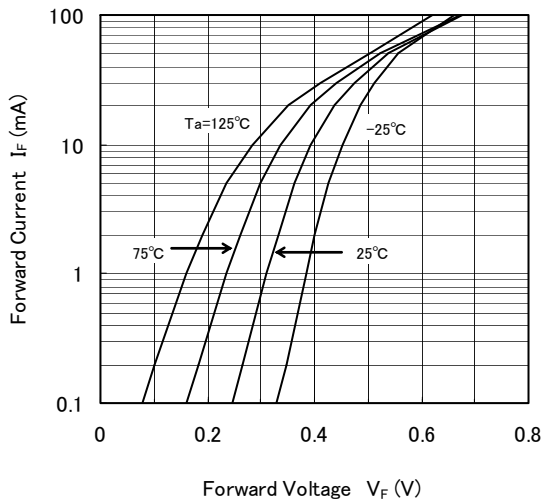
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN.	TYP.	MAX.	
Forward Voltage	V <sub>F1</sub>	I <sub>F</sub> =100mA	-	0.71	1	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =25V	-	-	2	μA

### NOTES ON USE

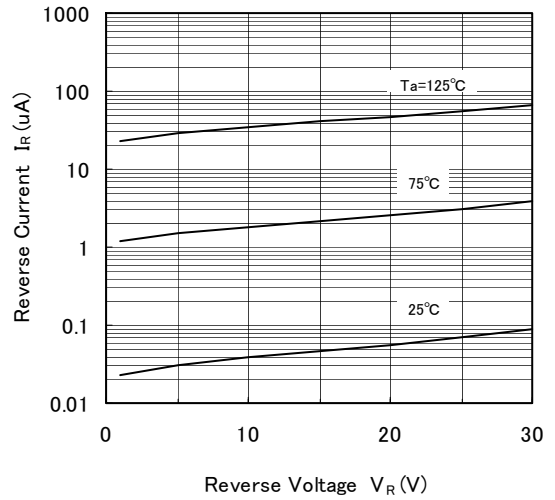
- Please keep away from mechanical stress to the product when mounting or after mounting.
- If the IC is mounted close to a board break line or fixed in screws, the IC or its electrodes may be caused damage as results of board deformation and mechanical stress.

## TYPICAL PERFORMANCE CHARACTERISTICS

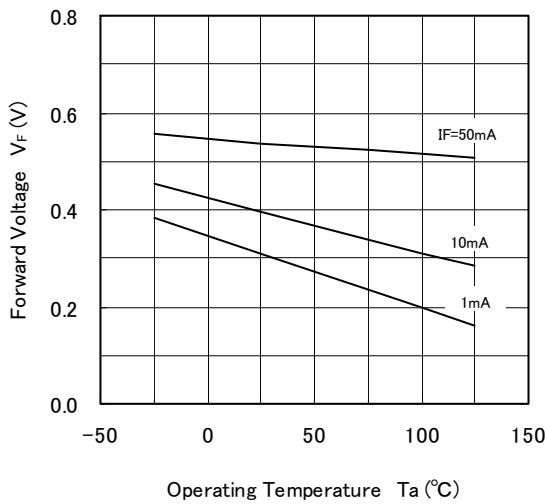
(1) Forward Current vs. Forward Voltage



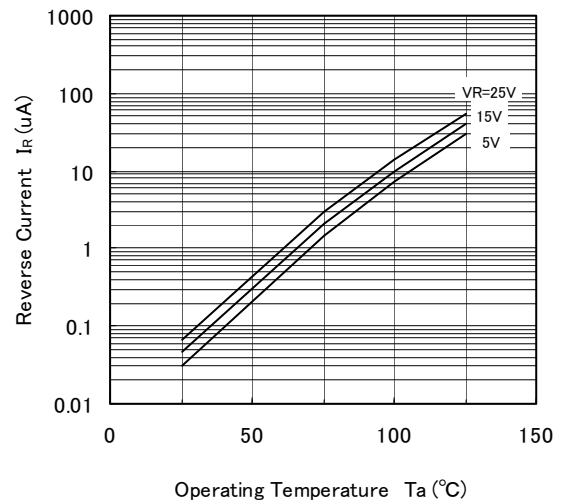
(2) Reverse Current vs. Reverse Voltage



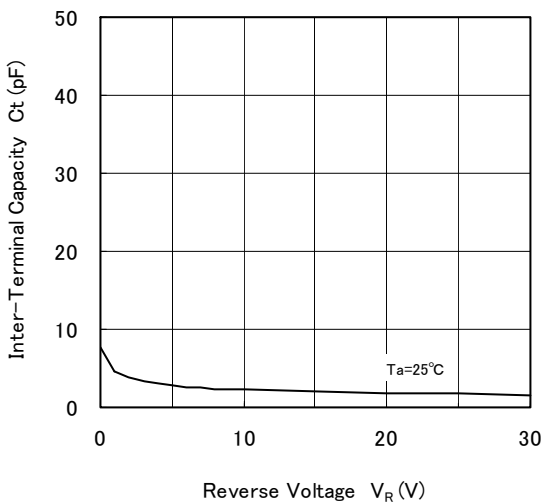
(3) Forward Voltage vs. Operating Temperature



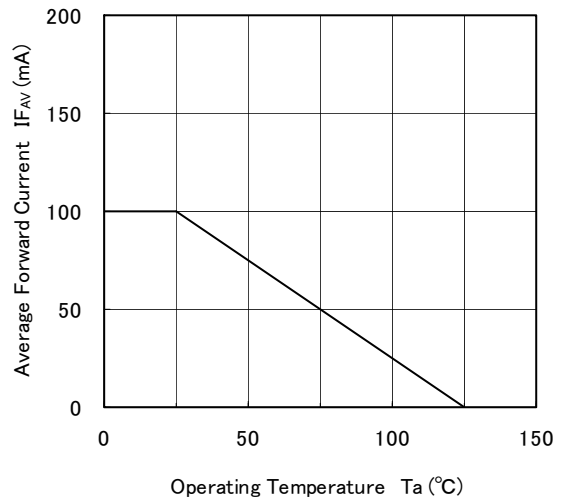
(4) Reverse Current vs. Operating Temperature



(5) Inter-Terminal Capacity vs. Reverse Voltage



(6) Average Forward Current vs. Operating Temperature



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